

54VHC/74VHC00•54VHCT/74VHCT00 Quad 2-Input NAND Gate

General Description

The VHC/VHCT00 is an advanced high-speed CMOS 2-Input NAND Gate fabricated with silicon gate CMOS technology. It achieves the high-speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 3 stages, including buffer output, which provide high noise immunity and stable output. An input protection circuit insures that 0V to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery backup. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

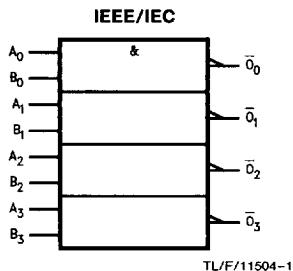
- High speed:
VHC $t_{PD} = 3.7$ ns (typ.) at $V_{CC} = 5V$
VHCT $t_{PD} = 5.0$ ns (typ.) at $V_{CC} = 5V$

- High noise immunity:
VHC $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
VHCT $V_{IH} = 2.0V$, $V_{IL} = 0.8V$
- Operating voltage:
VHC V_{CC} (opr) = 2.0V~5.5V
VHCT V_{CC} (opr) = 4.5V~5.5V
- Power down protection:
VHC inputs only
VHCT inputs and outputs
- Low noise:
VHC $V_{OLP} = 0.3V$ (typ)
VHCT $V_{OLP} = 0.4V$ (typ)
- Low power dissipation:
 $I_{CC} = 2 \mu A$ (max) at $T_A = 25^\circ C$
- Balanced propagation delays: $t_{PLH} \approx t_{PHL}$
- Pin and function compatible with 74HC/HCT00

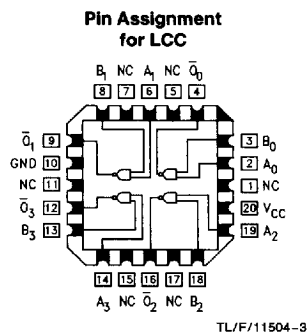
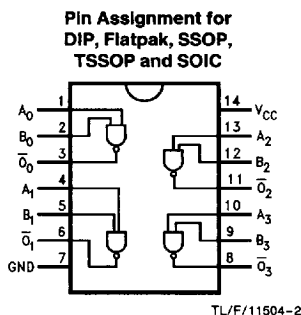
NOTE:

ADD EXTERNAL PULL UP RESISTOR TO VHCT OUTPUTS TO DRIVE CMOS INPUTS
MILITARY SPECIFICATIONS ARE PRELIMINARY

Logic Symbol



Connection Diagrams



Truth Table

A	B	O
L	L	H
L	H	H
H	L	H
H	H	L

Pin Names	Description
An, Bn	Inputs
On	Outputs

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	-0.5V to +7.0V
DC Input Voltage (V_{IN})	-0.5V to +7.0V
DC Output Voltage (V_{OUT})	
VHC	-0.5V to $V_{CC} + 0.5V$
VHCT*	-0.5V to 7.0V
Input Diode Current (I_{IK})	-20 mA
Output Diode Current (I_{OK})	
VHC	±20 mA
VHCT	-20 mA
DC Output Current (I_{OUT})	±25 mA
DC V_{CC} /GND Current (I_{CC})	±50 mA
Storage Temperature (T_{STG})	-65°C to +150°C
Lead Temperature (T_L)	
(Soldering, 10 seconds)	300°C

* $V_{OUT} > V_{CC}$ only if output is in H state

Note 1: Absolute Maximum Ratings are values beyond which the device may be damaged or have its useful life impaired. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation outside databook specifications.

Recommended Operating Conditions

Supply Voltage (V_{CC})	
VHC	2.0V to +5.5V
VHCT	4.5V to 5.5V
Input Voltage (V_{IN})	0V to +5.5V
Output Voltage (V_{OUT})	0V to V_{CC}
Operating Temperature (T_{OPR})	
54VHC/VHCT	-55°C to +125°C
74VHC/VHCT	-40°C to +85°C
Input Rise and Fall Time (t_r, t_f)	
$V_{CC} = 3.3V \pm 0.3V$ (VHC Only)	0 ns/V ~ 100 ns/V
$V_{CC} = 5.0V \pm 0.5V$	0 ns/V ~ 20 ns/V

DC Characteristics for 'VHC Family Devices

Symbol	Parameter	V _{CC} (V)	74VHC			54VHC		74VHC		Units	Conditions	
			T _A = 25°C			T _A = −55°C to +125°C		T _A = −40°C to +85°C				
			Min	Typ	Max	Min	Max	Min	Max			
V _{IH}	High Level Input Voltage	2.0 3.0–5.5	1.50			1.50		1.50		V		
			0.7 V _{CC}			0.7 V _{CC}		0.7 V _{CC}				
V _{IL}	Low Level Input Voltage	2.0 3.0–5.5			0.50 0.3 V _{CC}		0.50 0.3 V _{CC}		0.50 0.3 V _{CC}	V		
V _{OH}	High Level Output Voltage	2.0	1.9	2.0		1.9		1.9		V	V _{IN} = V _{IH} or V _{IL}	I _{OH} = −50 μA
		3.0	2.9	3.0		2.9		2.9				I _{OH} = −4 mA
		4.5	4.4	4.5		4.4		4.4				I _{OH} = −8 mA
		3.0 4.5	2.58 3.94			3.70		2.48 3.80		V		
V _{OL}	Low Level Output Voltage	2.0		0.0	0.1		0.1		0.1	V	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA
		3.0		0.0	0.1		0.1		0.1			
		4.5		0.0	0.1		0.1		0.1			
		3.0 4.5		0.36 0.36		0.50 0.50		0.44 0.44		V		I _{OL} = 4 mA I _{OL} = 8 mA
I _{IN}	Input Leakage Current	0–5.5			±0.1		±1.0		±1.0	μA	V _{IN} = 5.5V or GND	
I _{CC}	Quiescent Supply Current	5.5			2.0		160.0		20.0	μA	V _{IN} = V _{CC} or GND	

DC Characteristics for 'VHC Family Devices

Symbol	Parameter	V _{CC} (V)	74VHC		54VHC	74VHC	Units	Conditions
			T _A = 25°C		T _A = -55°C to +125°C	T _A = -40°C to +85°C		
			Typ	Limit	Limit	Limit		
*V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	5.0	0.3	0.8			V	C _L = 50 pF
*V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	5.0	-0.3	-0.8			V	C _L = 50 pF
*V _{IHD}	Minimum High Level Dynamic Input Voltage	5.0		3.5			V	C _L = 50 pF
*V _{ILD}	Maximum Low Level Dynamic Input Voltage	5.0		1.5			V	C _L = 50 pF

*Parameter guaranteed by design

DC Characteristics for 'VHCT Family Devices

Symbol	Parameter	V _{CC} (V)	74VHCT			54VHCT		74VHCT		Units	Conditions	
			T _A = 25°C			T _A = - 55°C to + 125°C		T _A = - 40°C to + 85°C				
			Min	Typ	Max	Min	Max	Min	Max			
V _{IH}	High Level Input Voltage	4.5 5.5	2.0 2.0				2.0 2.0		V			
V _{IL}	Low Level Input Voltage	4.5 5.5			0.8 0.8				0.8 0.8	V		
V _{OH}	High Level Output Voltage	4.5	3.15	3.65			3.15		V	V _{IN} = V _{IH}	I _{OH} = 50 μA	
		4.5	2.5			2.4		V	I _{OH} = 8 mA			
V _{OL}	Low Level Output Voltage	4.5	0.0		0.1				0.1	V	V _{IN} = V _{IH}	I _{OL} = 50 μA
		4.5			0.36				0.44	V		I _{OL} = 8 mA
I _{IN}	Input Leakage Current	0-5.5			± 0.1				± 1.0	μA	V _{IN} = 5.5V or GND	
I _{CC}	Quiescent Supply Current	5.5			2.0				20.0	μA	V _{IN} = V _{CC} or GND	
I _{CCT}	Maximum I _{CC} / Input	5.5			1.35				1.50	mA	V _{IN} = 3.4V Other Inputs = V _{CC} or GND	
I _{OPD}	Output Leakage Current (Power Down State)	0.0			0.5				5.0	μA	V _{OUT} = 5.5V	

DC Characteristics for 'VHCT Family Devices

Symbol	Parameter	V _{CC} (V)	74VHCT		54VHCT	74VHCT	Units	Conditions
			T _A = 25°C		T _A = -55°C to +125°C	T _A = -40°C to +85°C		
			Typ	Limit	Limit	Limit		
*V _{OLP}	Quiet Output Maximum Dynamic V _{OL}		0.4	0.8			V	C _L = 50 pF
*V _{OLV}	Quiet Output Minimum Dynamic V _{OL}		-0.4	-0.8			V	C _L = 50 pF
*V _{IHD}	Minimum High Level Dynamic Input Voltage			2.0			V	C _L = 50 pF
*V _{ILD}	Maximum Low Level Dynamic Input Voltage			0.8			V	C _L = 50 pF

*Parameter guaranteed by design.

AC Electrical Characteristics for 'VHC Family Devices

Symbol	Parameter	V _{CC} (V)	74VHC			54VHC		74VHC		Units	Conditions
			T _A = 25°C			T _A = -55°C to +125°C		T _A = -40°C to +85°C			
			Min	Typ	Max	Min	Max	Min	Max		
t _{PLH} , t _{PHL}	Propagation Delay	3.3 ± 0.3	5.5	7.9			1.0	9.5	ns	C _L = 15 pF	
			8.0	11.4			1.0	13.0		C _L = 50 pF	
		5.0 ± 0.5	3.7	5.5			1.0	6.5	ns	C _L = 15 pF	
			5.2	7.5			1.0	8.5		C _L = 50 pF	
C _{IN}	Input Capacitance		4	10			10		pF	V _{CC} = Open	
C _{PD}	Power Dissipation Capacitance		19							pF	(Note 1)

Note 1: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained from the equation: I_{CC (opr)} = C_{PD} * V_{CC} * f_{IN} + I_{CC}/4 (per gate).

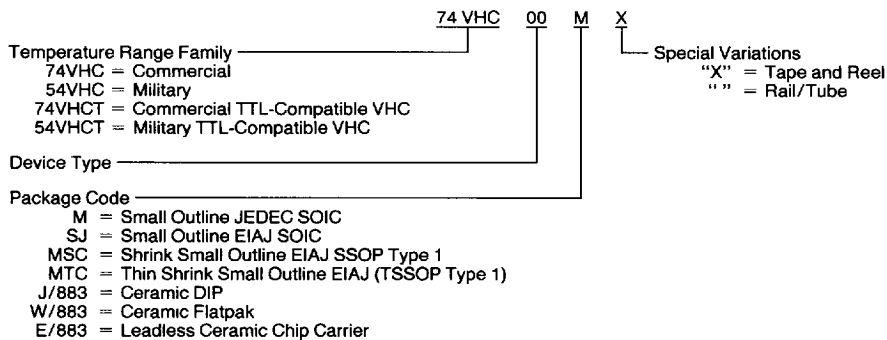
AC Electrical Characteristics for 'VHCT Family Devices

Symbol	Parameter	V _{CC} (V)	74VHCT			54VHCT		74VHCT		Units	Conditions
			T _A = 25°C			T _A = −55°C to +125°C		T _A = −40°C to +85°C			
			Min	Typ	Max	Min	Max	Min	Max		
t _{PLH} , t _{PHL}	Propagation Delay	5.0 ±0.5	5.0 6.9					1.0 8.0		ns	C _L = 15 pF
			5.5 7.9					1.0 9.0			C _L = 50 pF
C _{IN}	Input Capacitance		4 10					10		pF	V _{CC} = Open
C _{PD}	Power Dissipation Capacitance		17							pF	(Note 1)

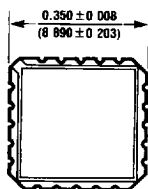
Note 1: C_{PD} is defined as the value of the internal equivalent capacitance, which is calculated from the operating current consumption without load. Average operating current can be obtained from the equation: I_{CC (opr)} = C_{PD} * V_{CC} * f_{IN} + I_{CC}/4 (per gate)

Ordering Information

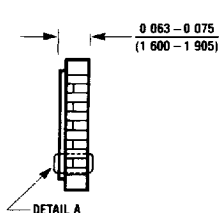
The device number is used to form part of a simplified purchasing code, where the package type and temperature range are defined as follows:



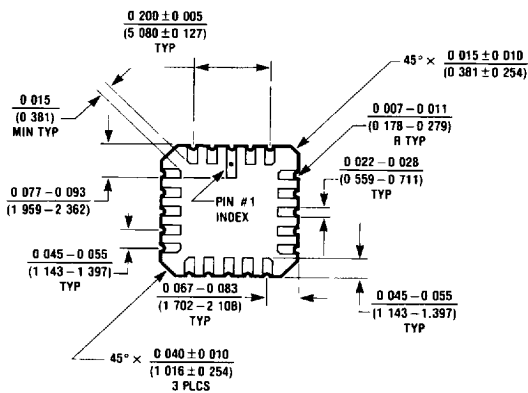
Physical Dimensions inches (millimeters)



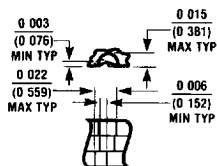
Top View



Side View



Bottom View

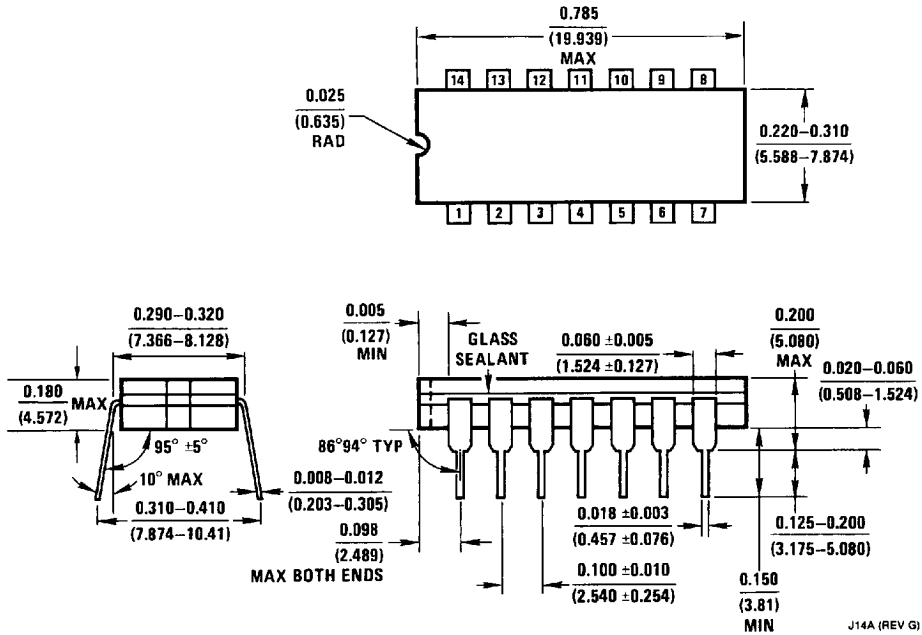


Detail A

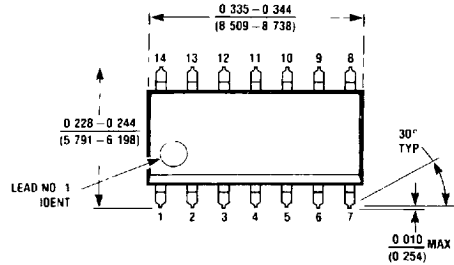
20-Lead Ceramic Leadless Chip Carrier, Type C (L)
Order Number 54VHC00E/883 or 54VHCT00E/883
NS Package Number E20A

L20A (REV D)

Physical Dimensions inches (millimeters) (Continued)

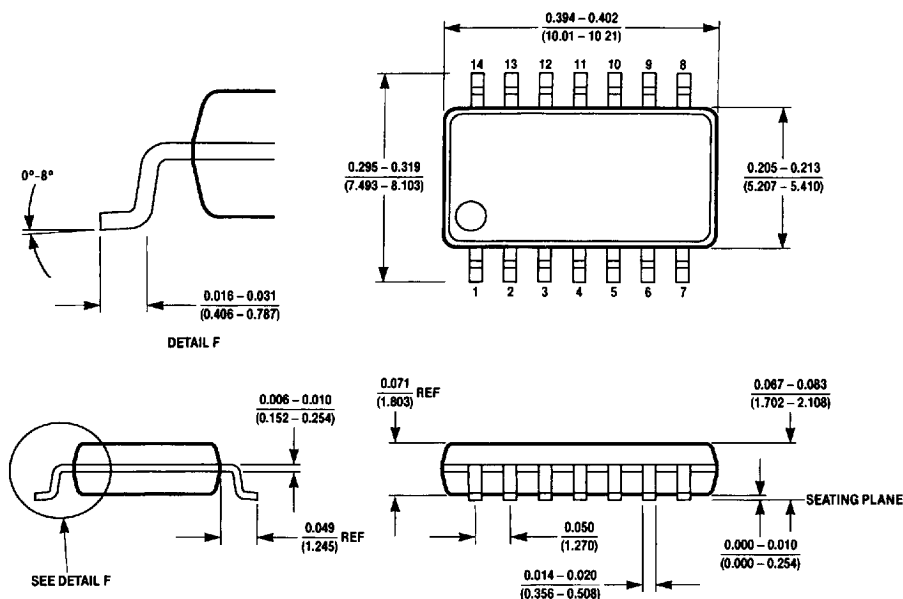


14-Lead Ceramic Dual-In-Line Package (D)
Order Number 54VHC00J/883 or 54VHCT00J/883
NS Package Number J14A



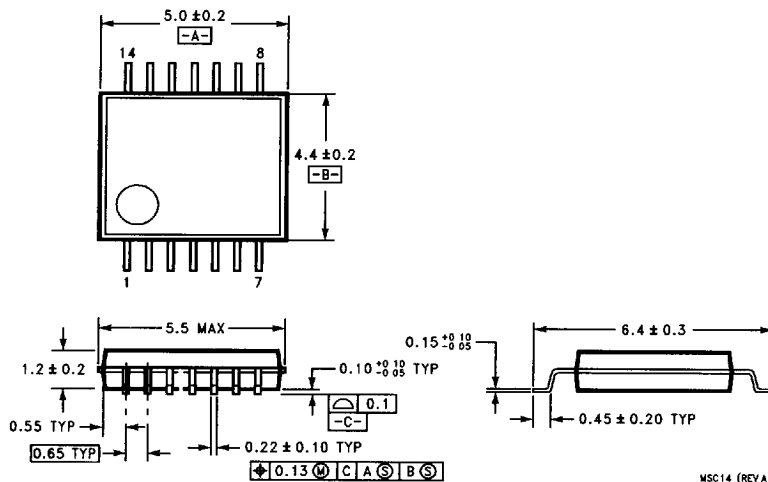
14-Lead Small Outline Integrated Circuit—JEDEC (M)
Order Number 74VHC00M, 74VHC00MX, 74VHCT00M or 74VHCT00MX
NS Package Number M14A

Physical Dimensions inches (millimeters) (Continued)



M14D (REV A)

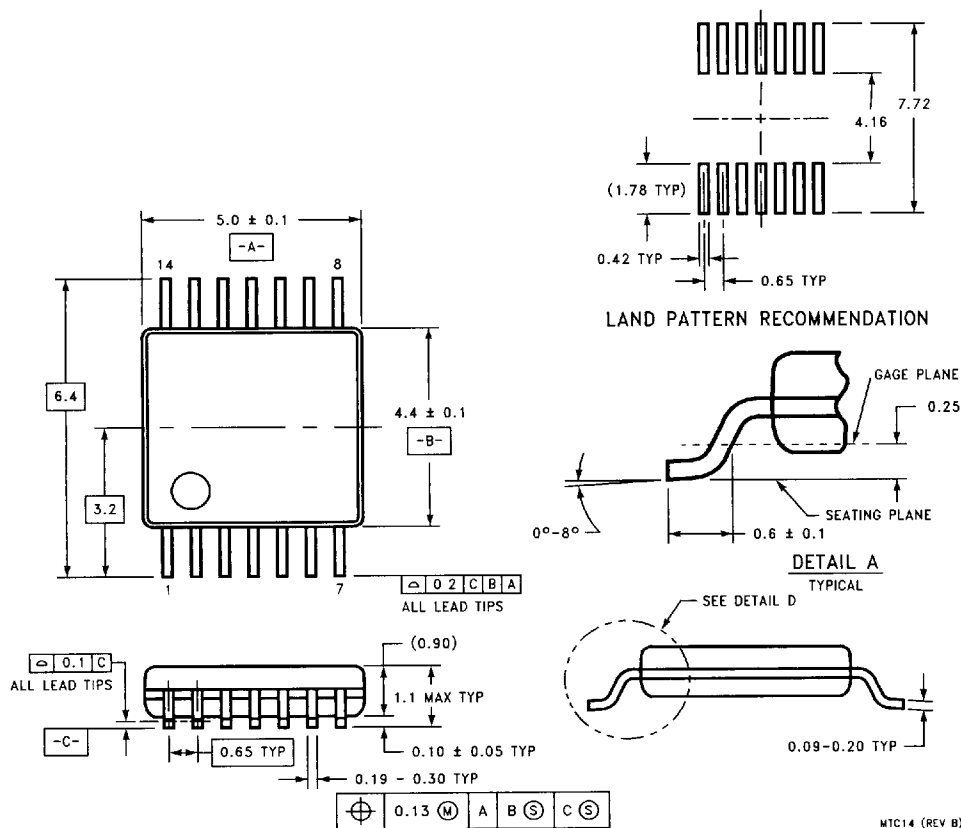
14-Lead Plastic EIAJ SOIC (SJ)
Order Number 74VHC00SJ, 74VHC00SJX, 74VHCT00SJ or 74VHCT00SJX
NS Package Number M14D



MSC14 (REV A)

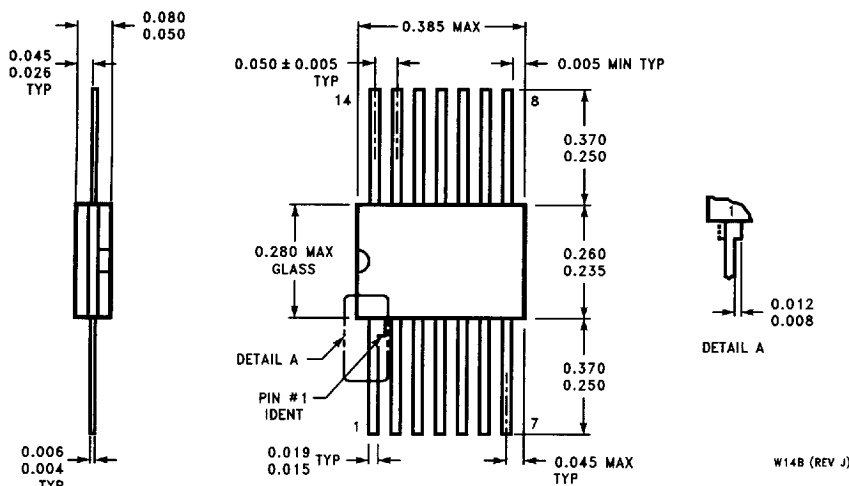
14-Lead Plastic EIAJ SSOP Type I (MSC)
Order Number 74VHC00MSCX or 74VHCT00MSCX
NS Package Number MSC14

Physical Dimensions inches (millimeters) (Continued)



Physical Dimensions inches (millimeters) (Continued)

Lit. # 118000-002



14-Lead Cerpack (F)
Order Number 54VHC00W/883 or 54VHCT00W/883
NS Package Number W14B

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